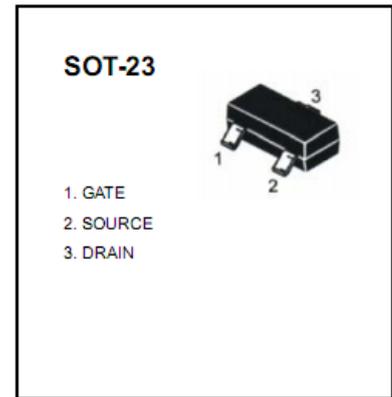
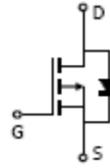


## SOT-23 Plastic-Encapsulate MOSET MOSFET(P-Channel)

### FEATURES

High Power and current handing capability  
Lead free product is acquired  
Surface Mount Packing

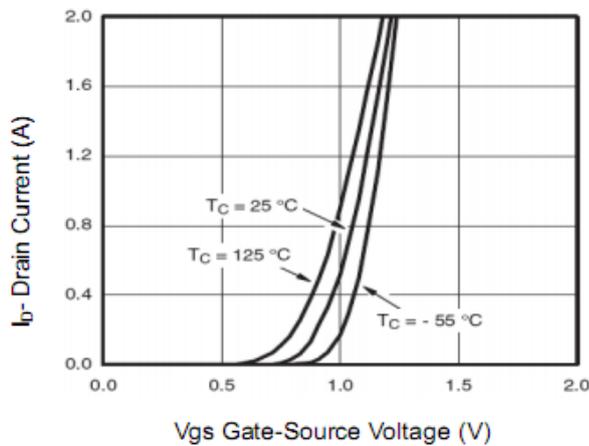


### MAXIMUM RATINGS (TA=25°C unless otherwise noted)

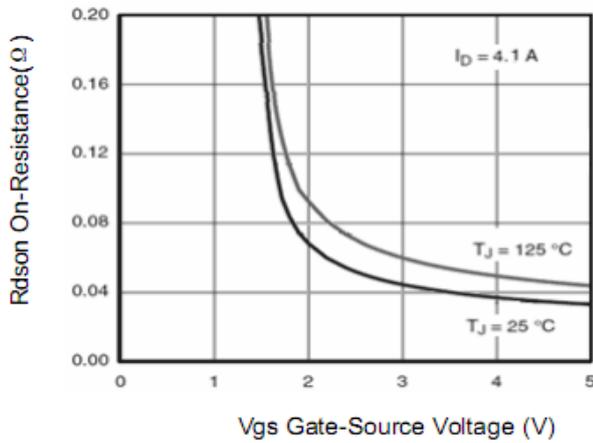
Symbol	Parameter	Value	Units
V <sub>DS</sub>	Drain-Source voltage	-20	V
V <sub>GS</sub>	Gate-Source voltage	±8	V
I <sub>D</sub>	Drain current (T <sub>c</sub> =25°C)	-4.1	A
P <sub>D</sub>	Power Dissipation	1.7	W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

### ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C unless otherwise specified)

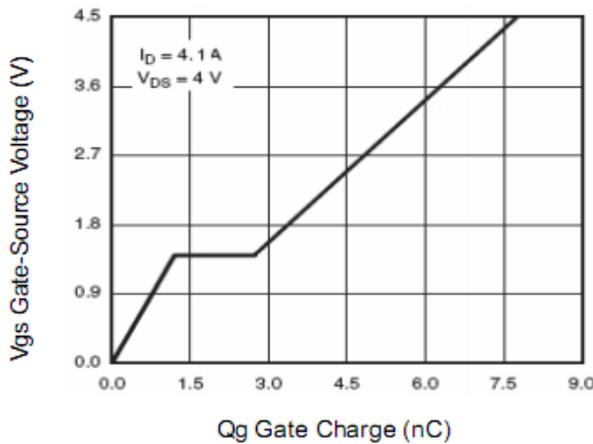
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-20			V
Gate-Threshold Voltage	V <sub>th(GS)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250 uA	-0.45	-0.7	-1	V
Gate-body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±8V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V			-1	uA
Drain-Source On-Resistance	r <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.1A		39	52	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-3A		58	75	mΩ
Forward Trans conductance	g <sub>fs</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-3.5A		8.5		S
Dynamic Characteristics						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-4V, V <sub>GS</sub> =0V, f=1MHz		740		pF
Output Capacitance	C <sub>oss</sub>			290		
Reverse Transfer Capacitance	C <sub>rss</sub>			190		
Switching Capacitance						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-4V, I <sub>D</sub> =-3.3A, V <sub>GS</sub> =-4.5V R <sub>GEN</sub> =1Ω		12		nS
Turn-on Rise Time	t <sub>r</sub>			35		nS
Turn-off Delay Time	t <sub>d(off)</sub>			30		nS
Turn-off Fall Time	t <sub>f</sub>			10		nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-4V, I <sub>D</sub> =-4.1A, V <sub>GS</sub> =-4.5V,		7.8		nC
Gate-Source Charge	Q <sub>gs</sub>			1.2		nC
Gate-Drain Charge	Q <sub>gd</sub>			1.6		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-1.3A			-1.2	V
Diode Forward Current	I <sub>S</sub>				-1.3	A



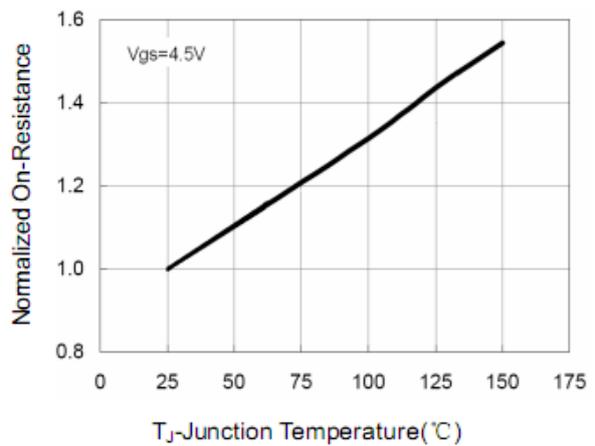
**Figure 7 Transfer Characteristics**



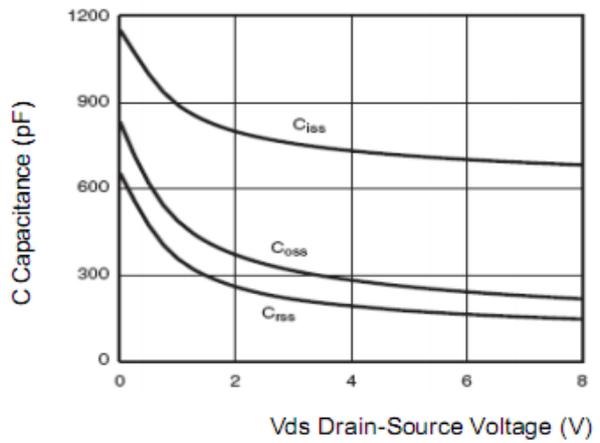
**Figure 9 Rdson vs Vgs**



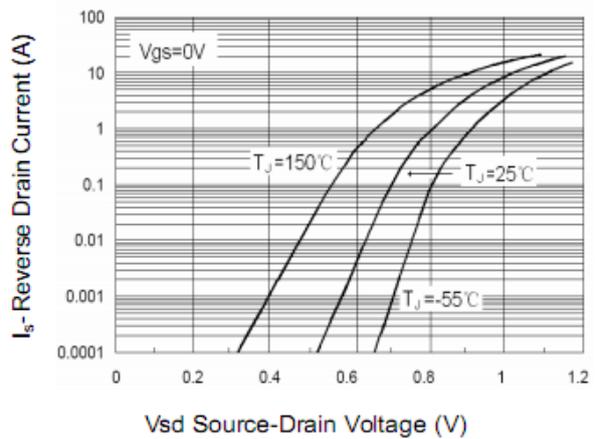
**Figure 11 Gate Charge**



**Figure 8 Drain-Source On-Resistance**



**Figure 10 Capacitance vs Vds**



**Figure 12 Source-Drain Diode Forward**

单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)